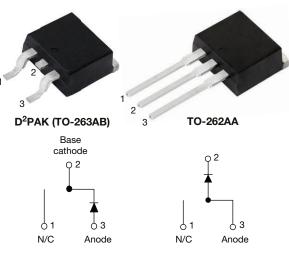
www.vishay.com

VS-MURB820-M3, VS-MURB820-1-M3

Vishay Semiconductors

Ultrafast Rectifier, 8 A FRED Pt[®]



VS-MURB820-M3

VS-MURB820-1-M3

PRIMARY CHARACTERISTICS				
I _{F(AV)}	8 A			
V _R	200 V			
V _F at I _F	0.895 V			
t _{rr}	35 ns			
T _J max.	175 °C			
Package	D ² PAK (TO-263AB), TO-262AA			
Circuit configuration	Single			

FEATURES

- Ultrafast recovery time
- · Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS	i			
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage	V _{RRM}		200	V
Average rectified forward current	I _{F(AV)}	Total device, rated V _R , T _C = 150 °C	8	
Non-repetitive peak surge current	I _{FSM}		100	А
Peak repetitive forward current	I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	16	
Operating junction and storage temperatures	TJ, T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	ARAMETER SYMBOL TEST CONDITIONS					UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-			
	VF	I _F = 8 A	-	-	0.975	V		
Forward voltage	VF	I _F = 8 A, T _J = 150 °C	-	-	0.895	0.895		
		$V_{R} = V_{R}$ rated	-	-	5			
Reverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	V µA pF		
Junction capacitance	CT	V _R = 200 V	-	25	-	pF		
Series inductance	LS	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

Revision: 25-Oct-17

1

RoHS

COMPLIANT

HALOGEN

FREE



VS-MURB820-M3, VS-MURB820-1-M3

www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY	CHARAC	TERISTICS (T_J :	= 25 °C unless oth	nerwise sp	ecified)		
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V _R = 30 V	-	-	35	
Reverse recovery time	+	I _F = 0.5 A, I _R = 1.0	A, I _{REC} = 0.25 A	-	-	25	ns
Reverse recovery time	t _{rr}	T _J = 25 °C		-	20	-	
		T _J = 125 °C		-	34	-	
Pools receivers ourrent	I _{RRM}	T _J = 25 °C	$I_F = 8 A$	-	1.7	-	А
Peak recovery current		T _J = 125 °C	dl _F /dt = 200 A/µs V _B = 160 V	-	4.2	-	
	0	T _J = 25 °C	VH - 100 V	-	23	-	nC
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	75	-	

THERMAL - MECHAN		CIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction-to-case	R _{thJC}		-	-	3.0	
Thermal resistance, junction-to-ambient	R _{thJA}		-	-	50	°C/W
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	2.0	-	g
weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking daviaa		Case style D ² PAK (TO-263AB)		MUR	B820	•
Marking device		Case style TO-262AA		MURE	3820-1	

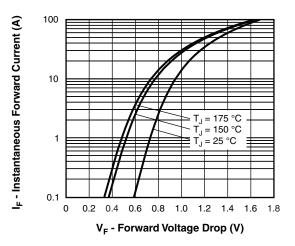


Fig. 1 - Typical Forward Voltage Drop Characteristics

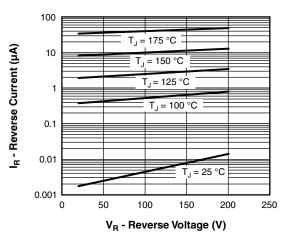


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



VS-MURB820-M3, VS-MURB820-1-M3

Vishay Semiconductors

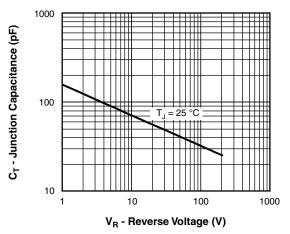


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

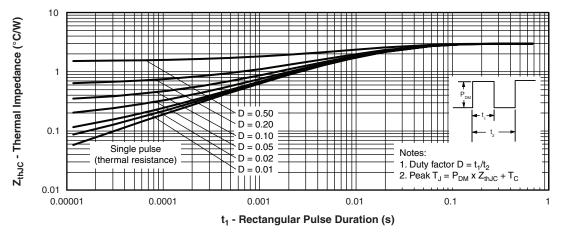
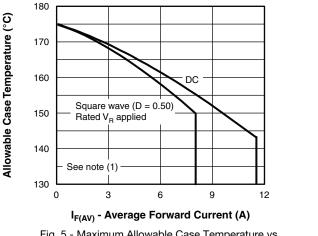
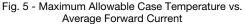
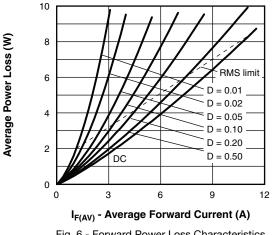


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics







For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

VS-MURB820-M3, VS-MURB820-1-M3



Vishay Semiconductors

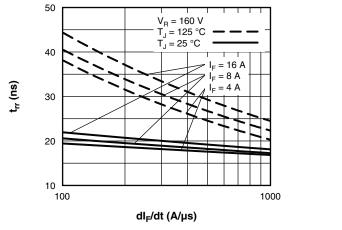
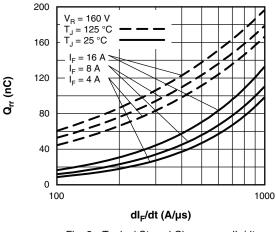
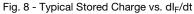


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R

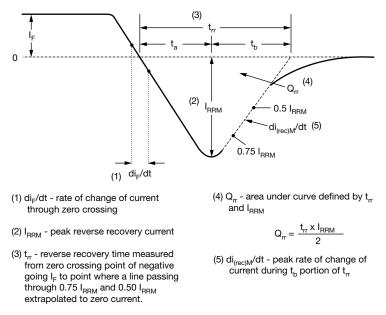
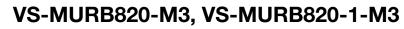


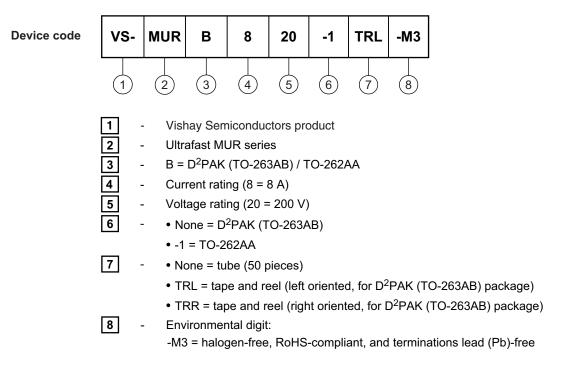
Fig. 9 - Reverse Recovery Waveform and Definitions





Vishay Semiconductors

ORDERING INFORMATION TABLE



	LINKS TO RELATED	DOCUMENTS
Dimensions —	D ² PAK (TO-263AB)	www.vishay.com/doc?96164
Dimensions	TO-262AA	www.vishay.com/doc?96165
Port marking information	ng information D ² PAK (TO-263AB) <u>www.vishay.com/doc?95444</u> TO-262AA <u>www.vishay.com/doc?95443</u>	www.vishay.com/doc?95444
		www.vishay.com/doc?95443
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?96424

Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN. MAX.		MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
		MIN.	MAX.	MIN.	MAX.	NOTES
	D1	6.86	8.00	0.270	0.315	3
	E	9.65	10.67	0.380	0.420	2, 3
	E1	7.90	8.80	0.311	0.346	3
	е	2.54 BSC		0.100 BSC		
	Н	14.61	15.88	0.575	0.625	
	L	1.78	2.79	0.070	0.110	
	L1	-	1.65	-	0.066	3
	L2	1.27	1.78	0.050	0.070	
	L3	0.25	0.25 BSC		BSC	
	L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 13-Jul-17

1

Document Number: 96164

For technical questions within your region: DiodesAmericas@vishav.com, DiodesAsia@vishav.com, DiodesEurope@vishav.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000



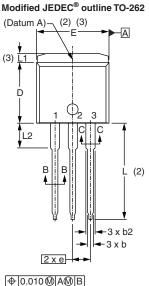
Outline Dimensions

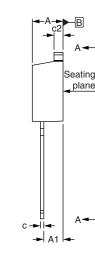


Vishay Semiconductors

TO-262AA

DIMENSIONS in millimeters and inches





F D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None





Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

CYMPOL	MILLIN	IETERS	INC	HES	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100) BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

 ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second dimensioner of the second dimensis and the second dimensioner of the second dimensioner of the the outmost extremes of the plastic body (3)

Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

1



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.